

Abstract

The present invention relates to the technical field of semiconductor manufacturing, and in particular to a semiconductor processing device comprising a radio-frequency system. The present invention provides a semiconductor processing device, comprising at least a reaction chamber, a radio-frequency receiving electrode, and a radio-frequency emitting electrode. The radio-frequency receiving electrode is arranged at the upper part inside the reaction chamber, and the radio-frequency emitting electrode is arranged at a lower part inside the reaction chamber and is used for emitting a radio-frequency power signal towards the upper part of the reaction chamber. The present invention introduces radio-frequency power from the bottom of the reaction chamber, and directly connects a connector to a matcher, thereby significantly improving the deposition rate of a substrate to be processed, and improving the process uniformity and stability.

(FIG. 3)